

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

STW11NM80

FEATURES

- Drain Current –I_D=11A@ T_C=25 $^\circ\!\!\mathbb{C}$
- Drain Source Voltage : V_{DSS}= 800V(Min)
- Static Drain-Source On-Resistance
 - : R_{DS(on)} = 0.4 Ω (Max) @ V_{GS}= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

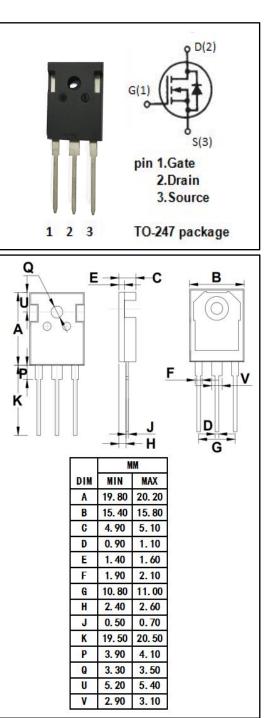
 Designed for use in switch mode power supplies and general purpose applications.



SYMBOL	PARAMETER	VALUE	UNIT		
V _{DSS}	Drain-Source Voltage	ain-Source Voltage 800			
V _{GS}	Gate-Source Voltage-Continuous ±30		V		
ID	Drain Current-Continuous		А		
I _{DM}	Drain Current-Single Pluse 4		A		
PD	Total Dissipation @Tc=25℃	Dissipation @T _c =25℃ 150			
TJ	Max. Operating Junction Temperature	-55~150	°C		
T _{stg}	Storage Temperature -55~150		°C		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.83	°C/W



isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	800		V
V _{GS(th)}	Gate Threshold Voltage	V_{DS} = V_{GS} ; I_D = 0.25mA	3	5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 5.5A		0.4	Ω
lgss	Gate-Body Leakage Current	V _{GS} = ±30V;V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800V; V _{GS} = 0		10	μA
V _{SD}	Forward On-Voltage	I _S = 11A; V _{GS} = 0		0.86	V

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